

# 2SB647, 2SB647A

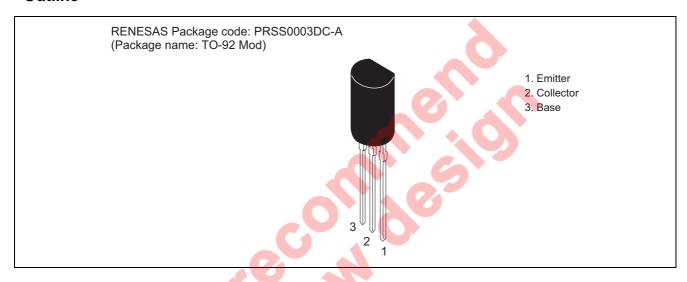
## Silicon PNP Epitaxial

REJ03G0648-0200 (Previous ADE-208-1025) Rev.2.00 Aug.10.2005

## **Application**

- Low frequency power amplifier
- Complementary pair with 2SD667/A

#### **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	2SB647	2SB647A	Unit
Collector to base voltage	$V_{CBO}$	-120	-120	V
Collector to emitter voltage	V <sub>CEO</sub>	-80	-100	V
Emitter to base voltage	$V_{EBO}$	<b>-</b> 5	<b>-</b> 5	V
Collector current	Ic	-1	<b>-1</b>	Α
Collector peak current	i <sub>C(peak)</sub>	-2	-2	Α
Collector power dissipation	Pc	0.9	0.9	W
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	°C

### **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

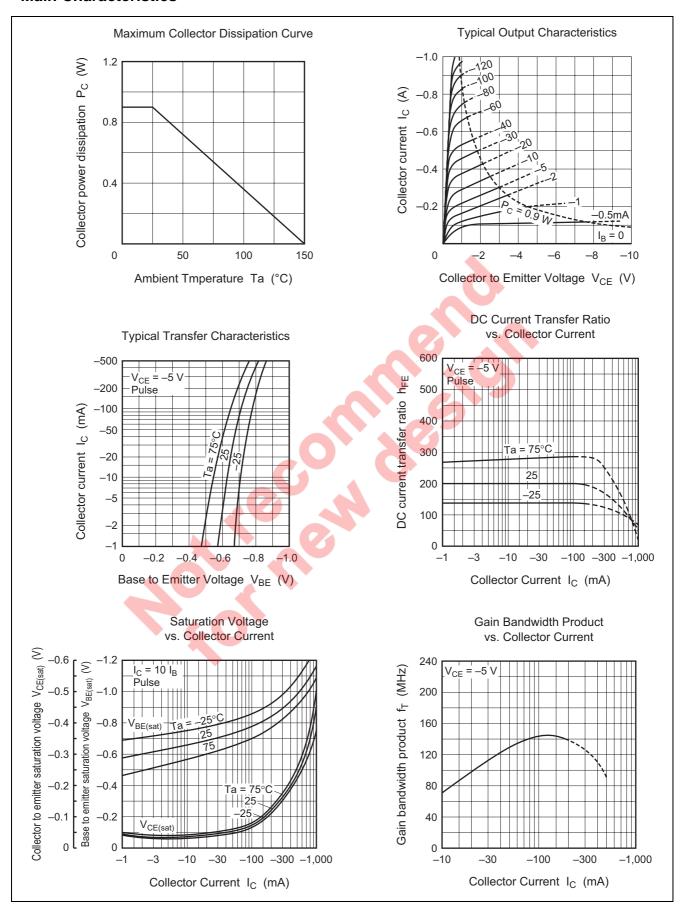
			2SB647		:	2SB647 <i>A</i>	4		
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	-120	_	_	-120	_	_	V	$I_C = -10 \mu\text{A},  I_E = 0$
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	-80	_	_	-100	_	_	V	$I_C = -1$ mA, $R_{BE} = \infty$
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	<del>-</del> 5	_	_	<del>-</del> 5	_	_	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I <sub>CBO</sub>			-10	_	_	-10	μΑ	$V_{CB} = -100 \text{ V}, I_E = 0$
DC current transfer ratio	h <sub>FE1</sub> *1	60	-	320	60	_	200		$V_{CE} = -5 \text{ V},$ $I_{C} = -150 \text{ mA*}^{2}$
	h <sub>FE2</sub>	30	_	_	30	_	_		$V_{CE} = -5 \text{ V},$ $I_{C} = -500 \text{ mA*}^{2}$
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>		_	-1	_	_	-1	V	$I_C = -500 \text{ mA},$ $I_B = -50 \text{ mA}^{*2}$
Base to emitter voltage	$V_{BE}$		_	-1.5	_		-1.5	V	$V_{CE} = -5 \text{ V},$ $I_{C} = -150 \text{ mA}^{*2}$
Gain bandwidth product	f⊤		140	_	-	140	<b>\</b>	MHz	$V_{CE} = -5 \text{ V},$ $I_{C} = -150 \text{ mA}$
Collector output capacitance	Cob		20	_	4	20	XC.	pF	$V_{CB} = -10 \text{ V}, I_{E} = 0$ f = 1 MHz

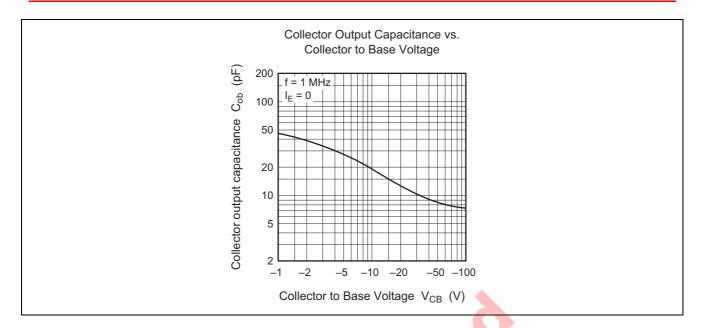
Notes: 1. The 2SB647 and 2SB647A are grouped by h<sub>FE1</sub> as follows.

#### 2. Pulse test

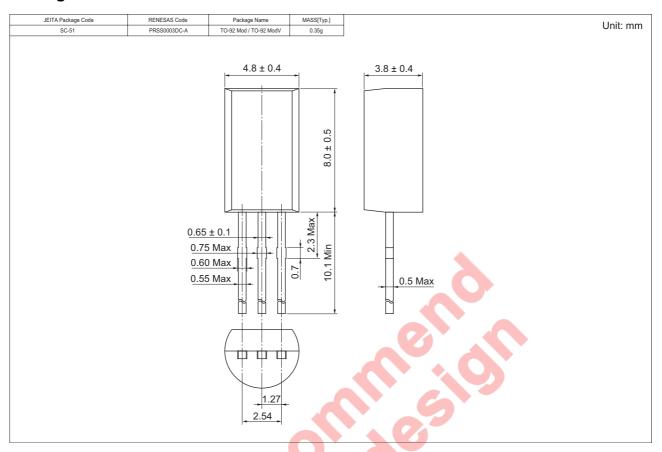
	В	С	D
2SB647	_	100 to 200	160 to 320
2SB647A	60 to 120	100 to 200	

#### **Main Characteristics**





## **Package Dimensions**



## **Ordering Information**

Part Name	Qu	antity	Shipping Container
2SB647CTZ-E	2500		Hold Box, Radial Taping
2SB647DTZ-E			
2SB647ABTZ-E			
2SB647ACTZ-E			

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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